NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL100** is Designed for

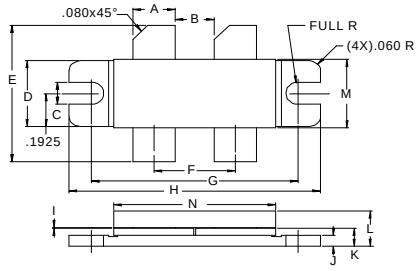
FEATURES:

- Input Matching Network
-
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	3.0 V
P_{DISS}	310 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	0.6 ^{O}C/W

PACKAGE STYLE .400 BAL FLG (C)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.120 / 3.05	.130 / 3.30
D	.380 / 9.65	.390 / 9.91
E	.780 / 19.81	.820 / 20.83
F	.435 / 11.05	
G	1.090 / 27.69	
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.082 / 2.08	.100 / 2.54
L		.205 / 5.21
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

ORDER CODE: ASI10585

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 100 mA	60			V
BV_{CEO}	I_C = 100 mA	30			V
BV_{EBO}	I_E = 50 mA	3.0			V
I_{CES}	V_{CE} = 28 V			10	mA
h_{FE}	V_{CE} = 5.0 V I_C = 3.0 A	15		70	---
P_G	V_{CE} = 24 V I_{CQ} = 2 X 100 mA f = 960 MHz	9.0			dB
IMD	P_{OUT} = 100 W		-32		dBc
η_C		45			%